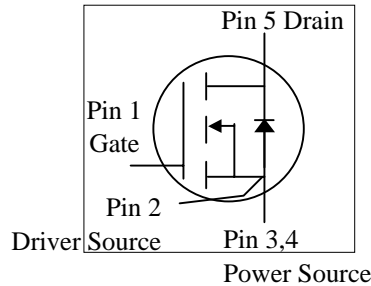




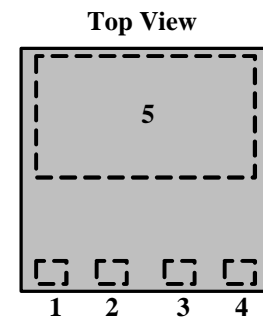
- ▼ 100% R<sub>g</sub> & UIS Test
- ▼ Low t<sub>rr</sub> / Q<sub>rr</sub>
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



BV <sub>DSS</sub>	650V
R <sub>DS(ON)</sub>	210mΩ
I <sub>D</sub> <sup>3,4</sup>	17.8A

**Description**

AP65SA210 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



PDFN 8X8\_HV

**Absolute Maximum Ratings @T<sub>j</sub>=25°C (unless otherwise specified)**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	650	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
V <sub>GS</sub>	Gate-Source Voltage, AC (f > 1Hz)	±30	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Drain Current, V <sub>GS</sub> @ 10V <sup>3,4</sup>	17.8	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Drain Current, V <sub>GS</sub> @ 10V <sup>3,4</sup>	11.2	A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	44	A
dv/dt	MOSFET dv/dt Ruggedness (V <sub>DS</sub> = 0 ...480V )	40	V/ns
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	125	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>7</sup>	2.5	W
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>5</sup>	200	mJ
dv/dt	Peak Diode Recovery dv/dt <sup>6</sup>	15	V/ns
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Value	Units
R <sub>thj-c</sub>	Maximum Thermal Resistance, Junction-case	1	°C/W
R <sub>thj-a</sub>	Maximum Thermal Resistance, Junction-ambient <sup>7</sup>	50	°C/W



# AP65SA210DDT8

## Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA	650	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.2A	-	-	210	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =6.2A	-	8.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =520V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±1	uA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =7.5A	-	44	70.4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =520V	-	11	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	22	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =300V	-	17	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =7.5A	-	27	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	44	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	19	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1535	2456	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =100V	-	57	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	7	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	4	8	Ω

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =6.2A, V <sub>GS</sub> =0V	-	0.8	-	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =11A, V <sub>GS</sub> =0V	-	150	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	1.2	-	uC

### Notes:

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test
- 3.Limited by max. junction temperature. Maximum duty cycle D=0.75
- 4.Ensure that the junction temperature does not exceed T<sub>Jmax</sub>.
- 5.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=90V , L=100mH , R<sub>G</sub>=25Ω , V<sub>GS</sub>=10V
- 6.I<sub>SD</sub> ≤ I<sub>D</sub>, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C
- 7.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

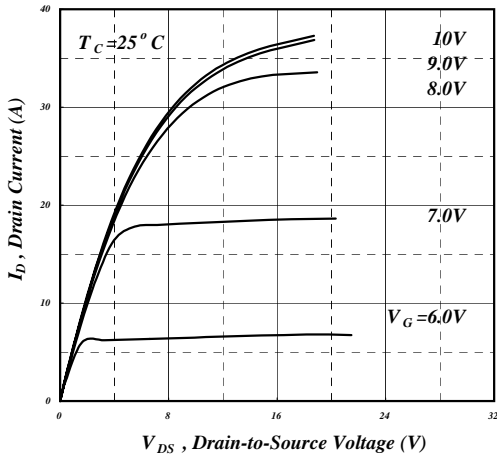


Fig 1. Typical Output Characteristics

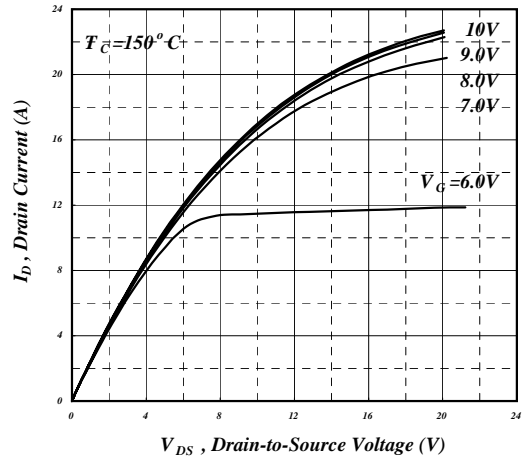


Fig 2. Typical Output Characteristics

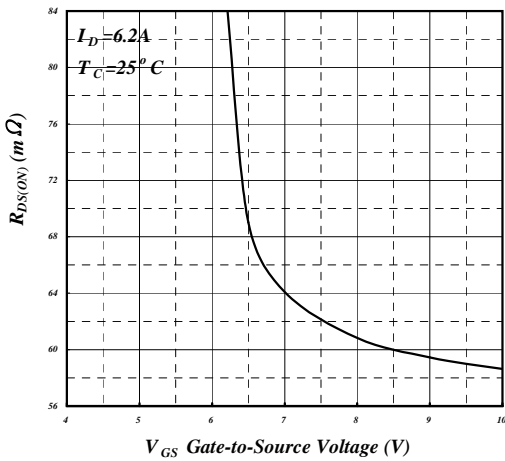


Fig 3. On-Resistance v.s. Gate Voltage

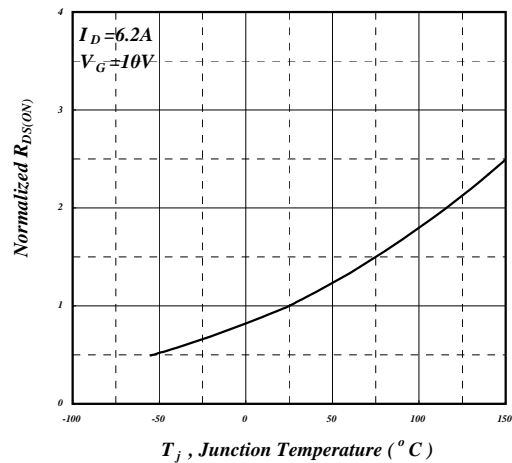


Fig 4. Normalized On-Resistance v.s. Junction Temperature

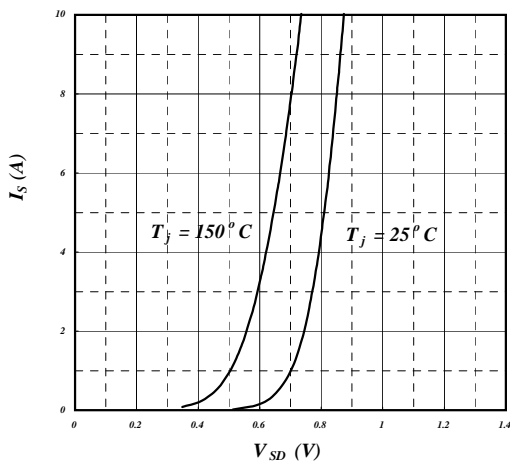


Fig 5. Forward Characteristic of Reverse Diode

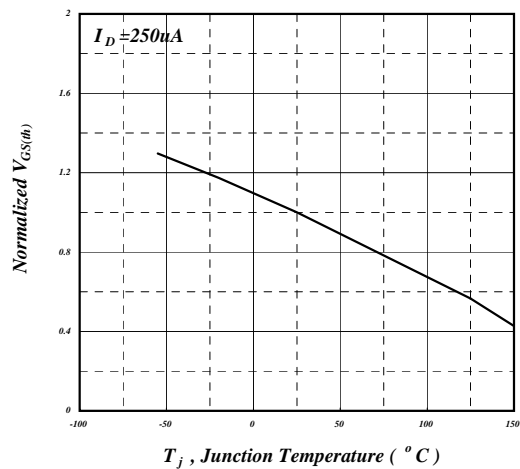


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

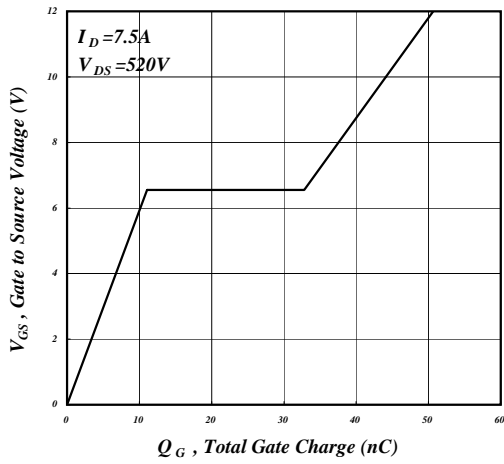


Fig 7. Gate Charge Characteristics

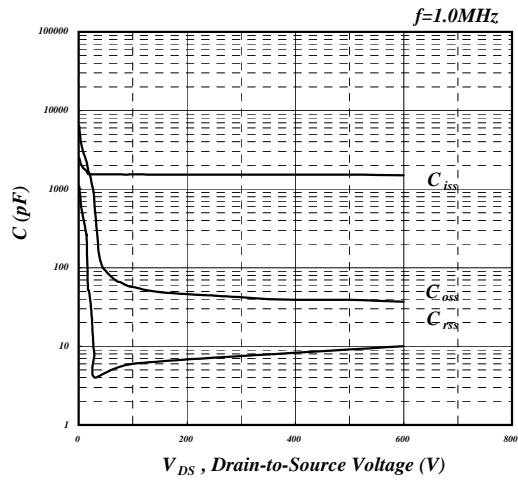


Fig 8. Typical Capacitance Characteristics

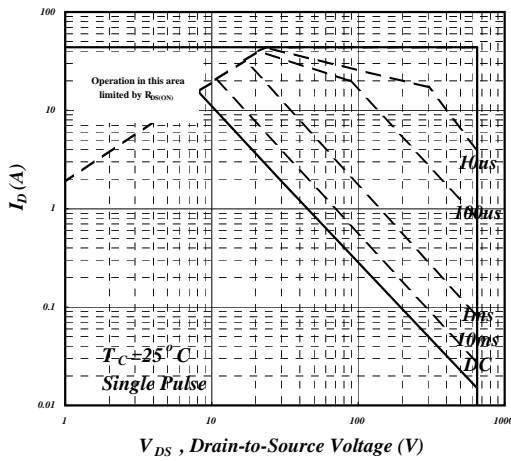


Fig 9. Maximum Safe Operating Area

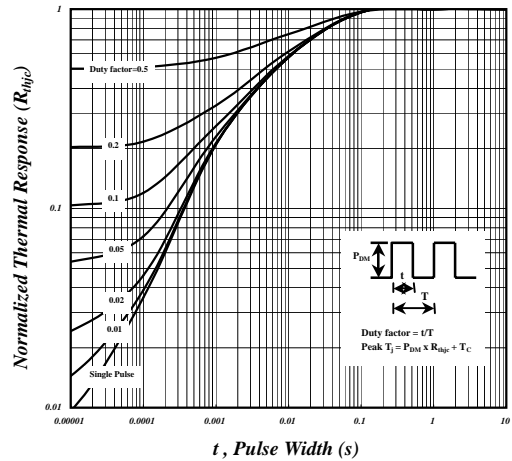


Fig 10. Effective Transient Thermal Impedance

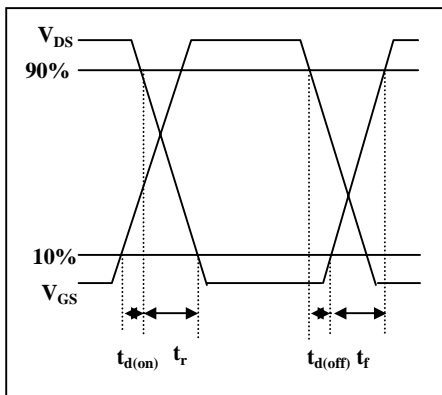


Fig 11. Switching Time Waveform

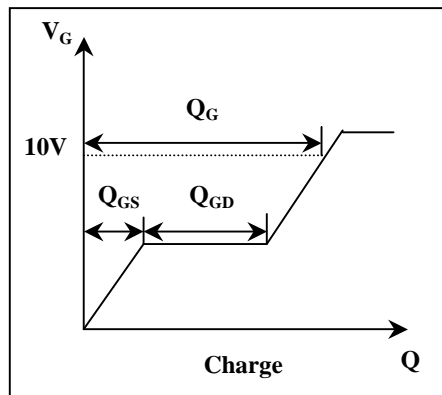


Fig 12. Gate Charge Waveform

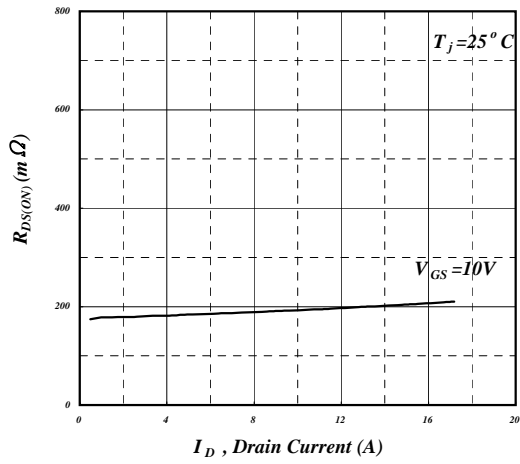


Fig 13. Typ. Drain-Source on State Resistance

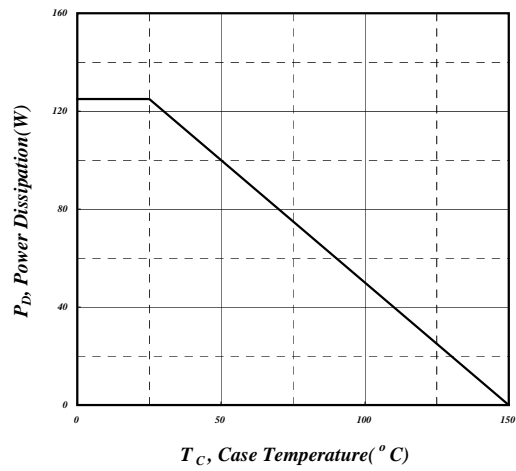


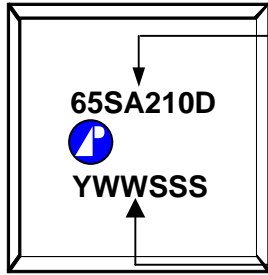
Fig 14. Total Power Dissipation



# AP65SA210DDT8

## MARKING INFORMATION

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Part Number

Date Code (YWWSSS)

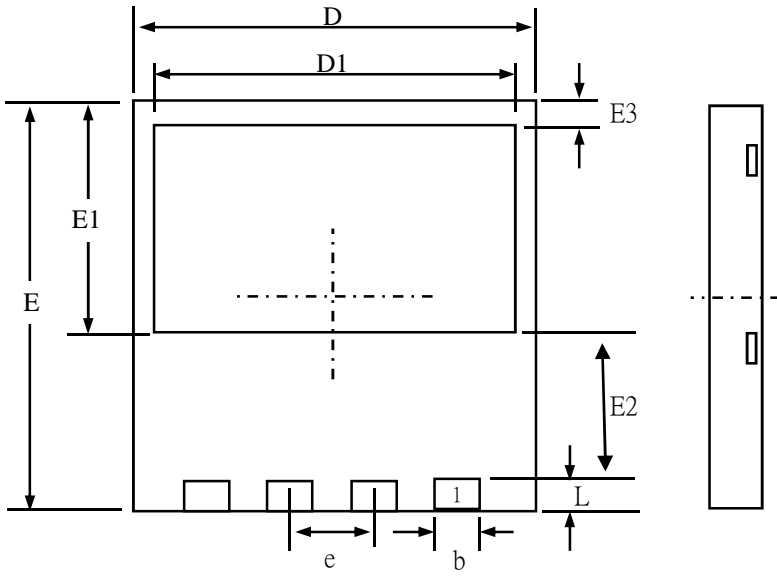
Y : Last Digit Of The Year

WW : Week

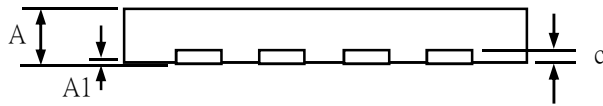
SSS : Sequence



**Package Outline : PDFN 8x8\_HV**



BOTTOM VIEW

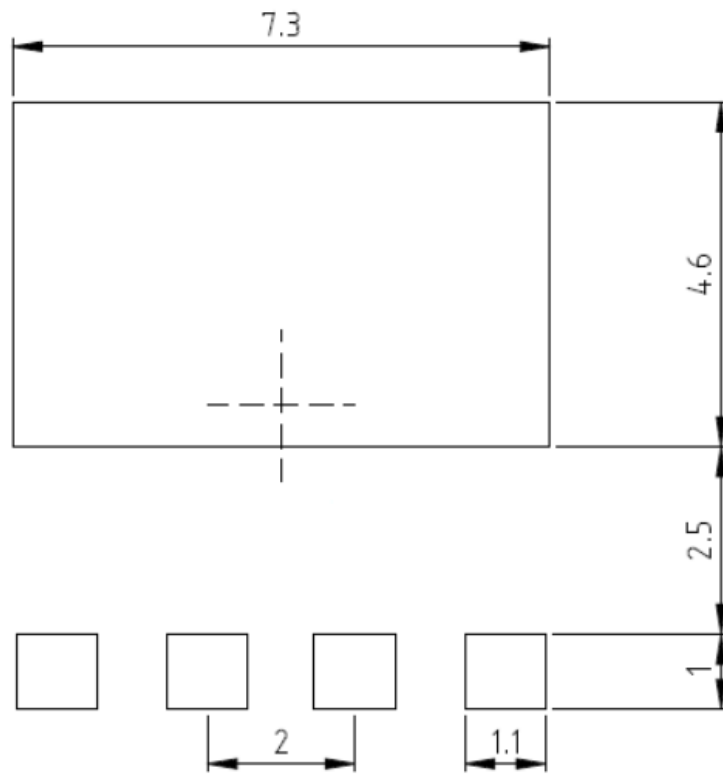


SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	0.75	0.93	1.10
A1	0.00	--	0.05
b	0.90	1.00	1.10
c	0.10	0.20	0.30
D	7.90	8.00	8.10
D1	7.10	7.20	7.30
E	7.90	8.00	8.10
E1	4.25	4.55	4.85
E2	2.65	2.75	2.85
E3	0.30	0.40	0.50
e	2.00BSC		
L	0.40	0.50	0.60

- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Burrs And Mold Flash.



PDFN 8x8 HV FOOTPRINT :



UNIT: mm